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October 2014

# FDMS8622

## N-Channel Shielded Gate PowerTrench<sup>®</sup> MOSFET

100 V, 16.5 A, 56 mΩ

### Features

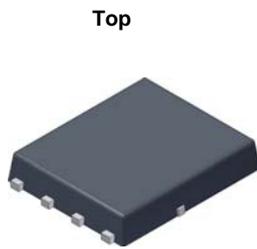
- Shielded Gate MOSFET Technology
- Max  $r_{DS(on)}$  = 56 mΩ at  $V_{GS} = 10$  V,  $I_D = 4.8$  A
- Max  $r_{DS(on)}$  = 88 mΩ at  $V_{GS} = 6$  V,  $I_D = 3.9$  A
- High performance trench technology for extremely low  $r_{DS(on)}$
- High power and current handling capability in a widely used surface mount package
- 100% UIL Tested
- Termination is Lead-free and RoHS Compliant

### General Description

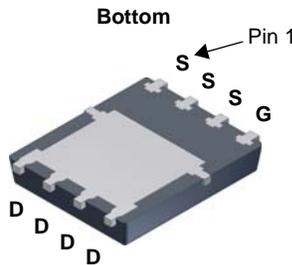
This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench<sup>®</sup> process that incorporates Shielded Gate technology. This process has been optimized for  $r_{DS(on)}$ , switching performance and ruggedness.

### Applications

- POE Protection Switch
- DC-DC Switch

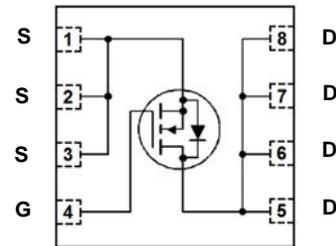


Top



Bottom

Pin 1



Power 56

### MOSFET Maximum Ratings $T_A = 25$ °C unless otherwise noted

Symbol	Parameter	Rated	Units
$V_{DS}$	Drain to Source Voltage	100	V
$V_{GS}$	Gate to Source Voltage	$\pm 20$	V
$I_D$	Drain Current -Continuous	$T_C = 25$ °C	16.5
	-Continuous	$T_A = 25$ °C (Note 1a)	4.8
	-Pulsed		30
$E_{AS}$	Single Pulse Avalanche Energy	(Note 3)	12
$P_D$	Power Dissipation	$T_C = 25$ °C	31
	Power Dissipation	$T_A = 25$ °C (Note 1a)	2.5
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	°C

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	(Note 1)	4	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	50	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS8622	FDMS8622	Power56	13 "	12 mm	3000 units

FDMS8622 N-Channel Shielded Gate PowerTrench<sup>®</sup> MOSFET

## Electrical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Off Characteristics

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$ , $V_{GS} = 0\text{ V}$	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^\circ\text{C}$		69		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 80\text{ V}$ , $V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{ V}$ , $V_{DS} = 0\text{ V}$			$\pm 100$	nA

### On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^\circ\text{C}$		-8		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}$ , $I_D = 4.8\text{ A}$		45	56	m $\Omega$
		$V_{GS} = 6\text{ V}$ , $I_D = 3.9\text{ A}$		62	88	
		$V_{GS} = 10\text{ V}$ , $I_D = 4.8\text{ A}$ , $T_J = 125\text{ }^\circ\text{C}$		78	97	
$g_{FS}$	Forward Transconductance	$V_{DD} = 5\text{ V}$ , $I_D = 4.8\text{ A}$		9		S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 50\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$		301	400	pF
$C_{oss}$	Output Capacitance			70	95	pF
$C_{rss}$	Reverse Transfer Capacitance			3.6	5	pF
$R_g$	Gate Resistance			1.0		$\Omega$

### Switching Characteristics

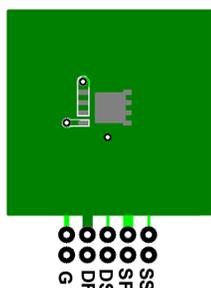
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 50\text{ V}$ , $I_D = 4.8\text{ A}$ , $V_{GS} = 10\text{ V}$ , $R_{GEN} = 6\text{ }\Omega$		5.7	11	ns
$t_r$	Rise Time			1.7	10	ns
$t_{d(off)}$	Turn-Off Delay Time			10.2	18	ns
$t_f$	Fall Time			2.1	10	ns
$Q_{g(TOT)}$	Total Gate Charge		$V_{GS} = 0\text{ V to }10\text{ V}$	$V_{DD} = 50\text{ V}$ , $I_D = 4.8\text{ A}$	5	7
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0\text{ V to }5\text{ V}$	2.8		4	nC
$Q_{gs}$	Total Gate Charge		1.4		2.8	nC
$Q_{gd}$	Gate to Drain "Miller" Charge		1.3		2.6	nC

### Drain-Source Diode Characteristics

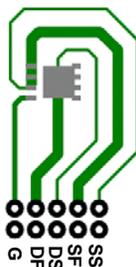
$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}$ , $I_S = 4.8\text{ A}$ (Note 2)		0.8	1.3	V
		$V_{GS} = 0\text{ V}$ , $I_S = 1.9\text{ A}$ (Note 2)		0.8	1.2	
$t_{rr}$	Reverse Recovery Time	$I_F = 4.8\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$		38	60	ns
$Q_{rr}$	Reverse Recovery Charge			30	48	nC

#### Notes:

- $R_{\theta JA}$  is determined with the device mounted on a  $1\text{ in}^2$  pad 2 oz copper pad on a  $1.5 \times 1.5\text{ in.}$  board of FR-4 material.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a)  $50\text{ }^\circ\text{C/W}$  when mounted on a  $1\text{ in}^2$  pad of 2 oz copper



b)  $125\text{ }^\circ\text{C/W}$  when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width <  $300\text{ }\mu\text{s}$ , Duty cycle < 2.0%.

3. Starting  $T_J = 25\text{ }^\circ\text{C}$ ; N-ch:  $L = 0.1\text{ mH}$ ,  $I_{AS} = 16\text{ A}$ ,  $V_{DD} = 90\text{ V}$ ,  $V_{GS} = 10\text{ V}$ .

**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted

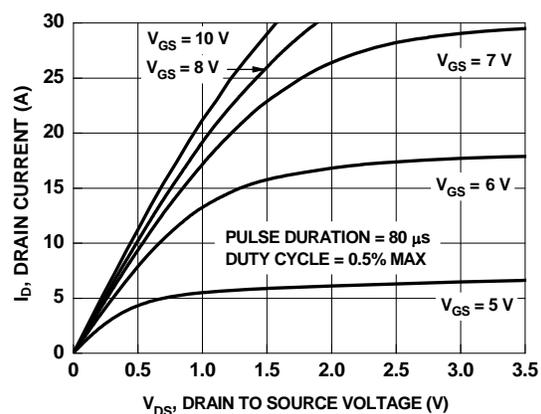


Figure 1. On Region Characteristics

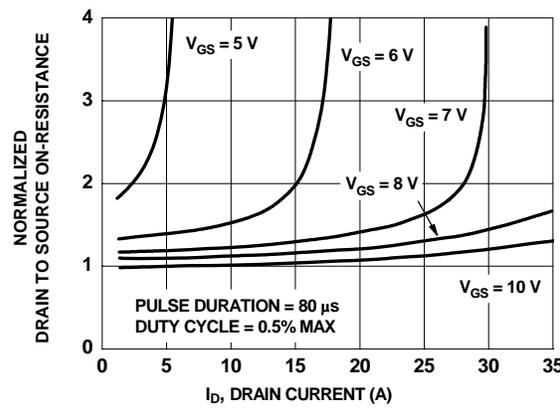


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

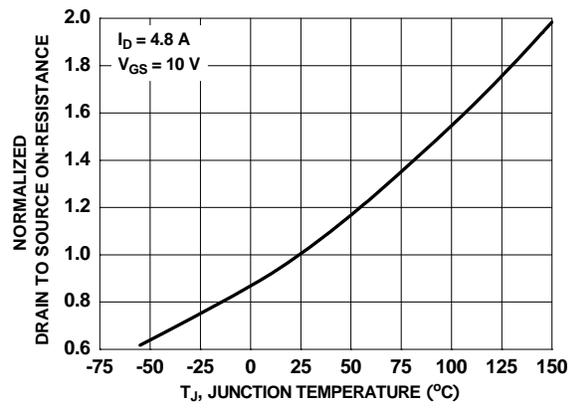


Figure 3. Normalized On Resistance vs Junction Temperature

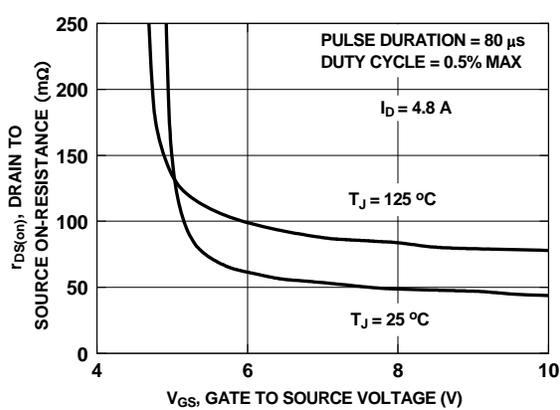


Figure 4. On-Resistance vs Gate to Source Voltage

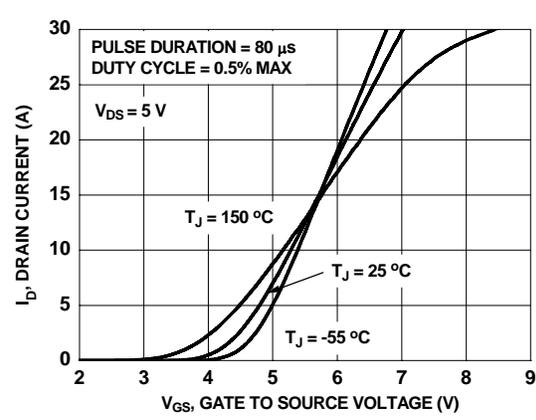


Figure 5. Transfer Characteristics

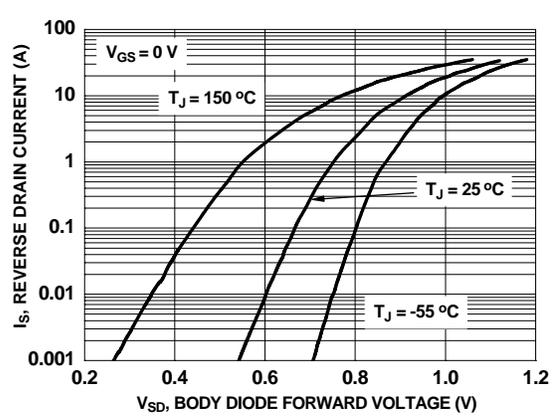
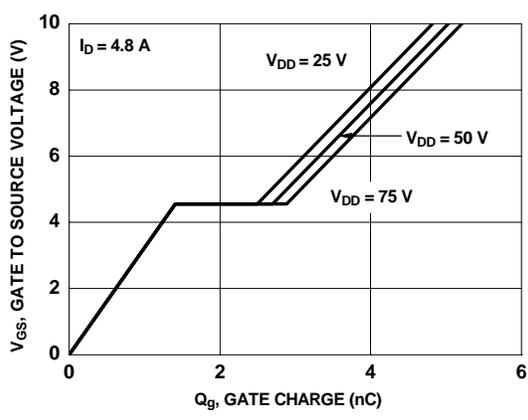
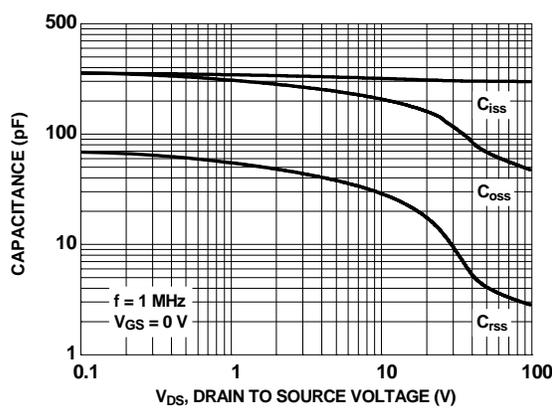


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

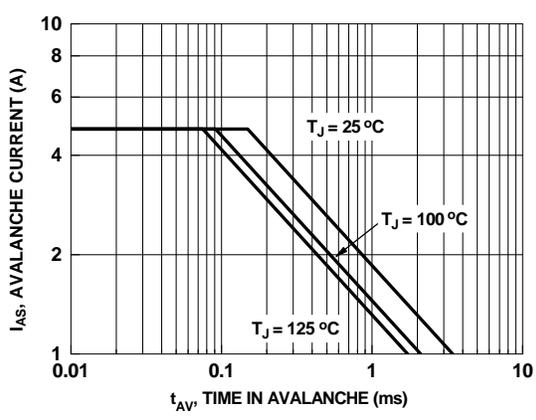
**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted



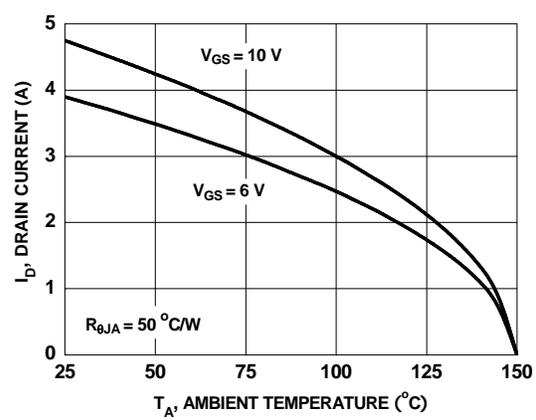
**Figure 7. Gate Charge Characteristics**



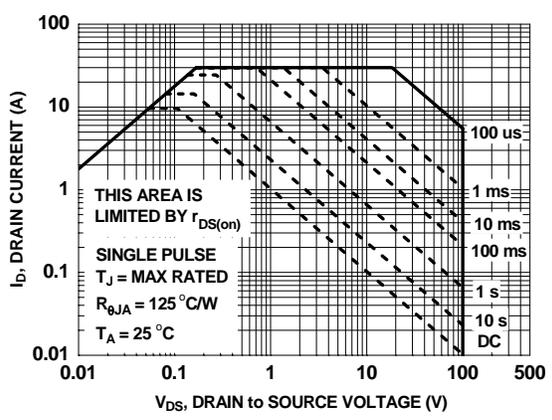
**Figure 8. Capacitance vs Drain to Source Voltage**



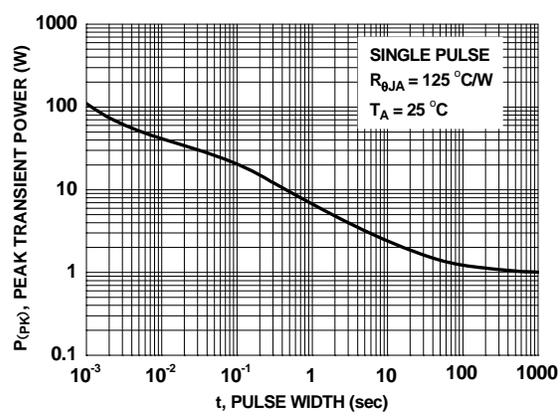
**Figure 9. Unclamped Inductive Switching Capability**



**Figure 10. Maximum Continuous Drain Current vs Ambient Temperature**

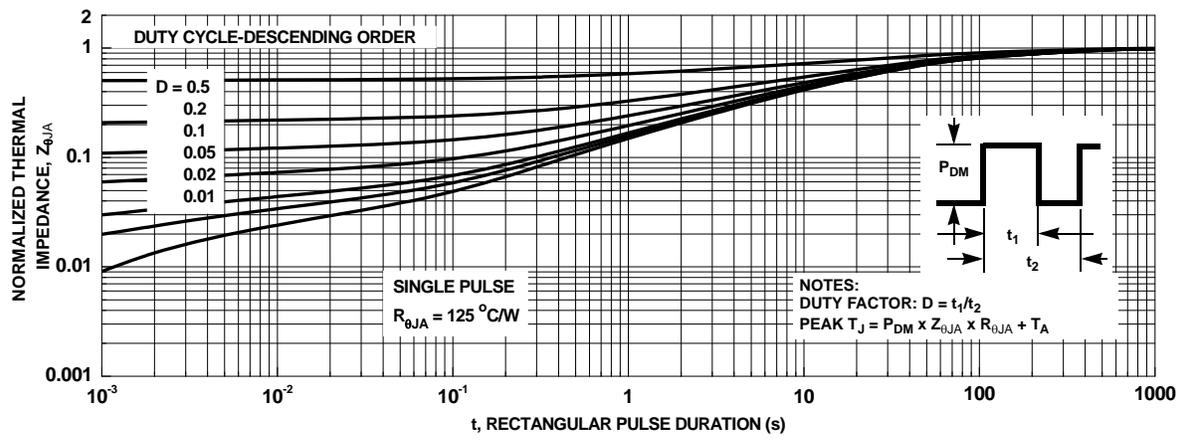


**Figure 11. Forward Bias Safe Operating Area**

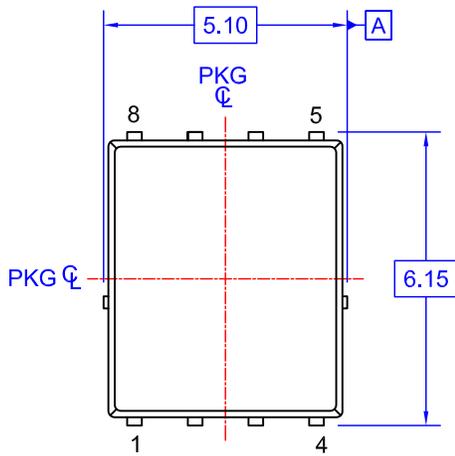


**Figure 12. Single Pulse Maximum Power Dissipation**

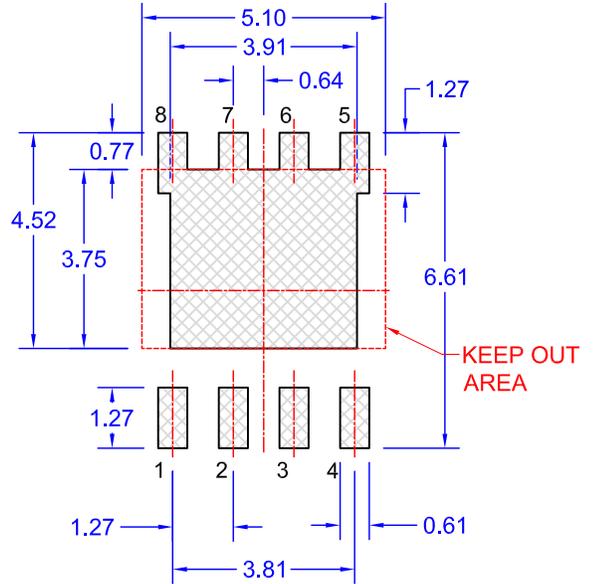
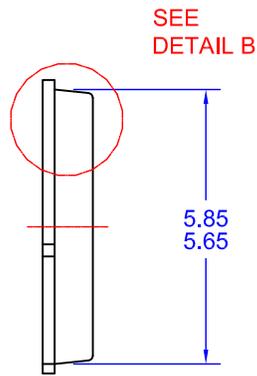
**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted



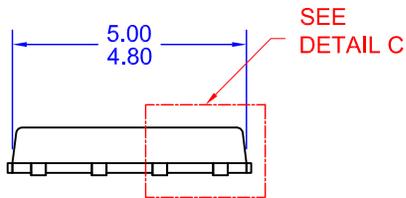
**Figure 13. Junction-to-Ambient Transient Thermal Response Curve**



TOP VIEW

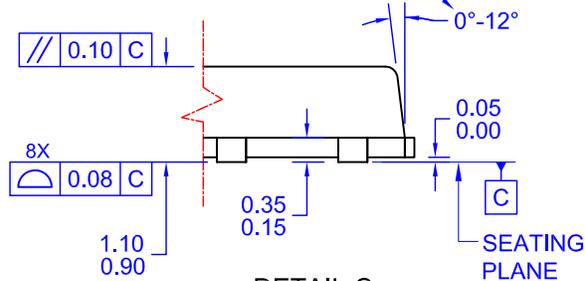


LAND PATTERN RECOMMENDATION

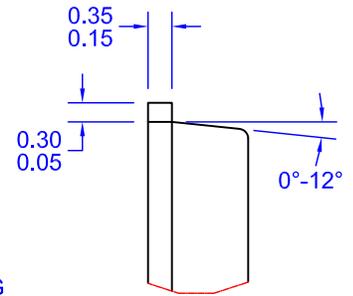


SIDE VIEW

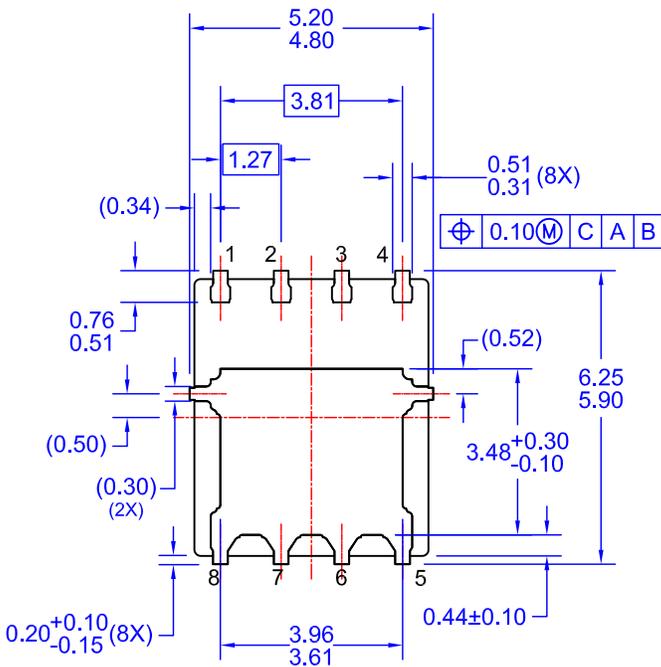
OPTIONAL DRAFT ANGLE MAY APPEAR ON FOUR SIDES OF THE PACKAGE



DETAIL C  
SCALE: 2:1



DETAIL B  
SCALE: 2:1



BOTTOM VIEW

NOTES: UNLESS OTHERWISE SPECIFIED

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- B. DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
- E. IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.
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